

AMENDMENTS TO CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method for detecting an STI void of a semiconductor wafer, comprising steps of:

assigning a test region in a ~~predetermined~~ region of the wafer;

forming, in a test region, active areas, trenches between the active areas, and gate lines intersecting with the active areas, said trenches being filled with dielectric, and said active areas having their adjacent portion reaching ~~at least a predetermined-length~~ longer than at least two gate lines; and

measuring ~~the electric values of between~~ said gate lines to determine whether there is a void formed in the trench.

2. (Original) The method as claimed in Claim 1, wherein said active areas in the testing region are formed as parallel strips.

3. (Original) ~~The A method as claimed in Claim 1~~ for detecting an STI void of a semiconductor wafer, comprising the steps of:

assigning a test region in a region of the wafer;

forming, in a test region, active areas, trenches between the active areas, and gate lines intersecting with the active areas, said trenches being filled with dielectric; and

measuring electric values between said gate lines to determine whether there is a void formed in the trench,

wherein odd ones of said gate lines are connected together, while even ones of the gate lines are connected together, so as to form a dual-comb structure.

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4. (Currently Amended) The method as claimed in Claim 3, wherein said measuring step is to measure the potentials ~~of~~ between the comb structure of the odd gate lines and the comb structure of the even gate lines.

5. (Currently Amended) The method as claimed in Claim 1, wherein the testing region is formed on a ~~predetermined~~ cutting line of the wafer.

6. (Canceled)

7. (Canceled)

8. (Canceled)